

IN THE SPECIFICATION

Please delete the abstract at page 8, lines 2-12, and insert a new abstract as follows:

A method of manufacturing a semiconductor device includes forming a first interlayer insulation film on a semiconductor substrate, depositing a first metal film on the first interlayer insulation film, depositing an antireflection film including a dielectric layer on an upper surface of the first metal film, patterning the first metal film and the antireflection film to form a lower electrode having the antireflection film on an upper surface thereof, forming a second interlayer insulation film on the antireflection film, forming first and second openings in a first region and in a second region in the second interlayer insulation film, respectively, removing a portion of the antireflection film where the second opening is formed, depositing a second metal film on the second interlayer insulation film, and removing the second metal film except in the first and second openings to form an upper electrode in the first opening, and a contact in the second opening.